



**KULLIYAH OF ENGINEERING**

**END OF SEMESTER EXAMINATION  
SEMESTER II, 2014/2015 SESSION**

Programme	: <b>Engineering</b>	Level of Study	: <b>UG 2</b>
Time	: <b>2.30 pm -5.30 pm</b>	Date	: <b>02/06/2015</b>
Duration	: <b>3 Hrs</b>		
Course Code	: <b>ECE 2133</b>	Section(s)	: <b>1-2</b>
Course Title	: <b>Electronic Circuits</b>		

This Question Paper Consists of 7 (**Seven**) Printed Pages (Including Cover Page) with 5 (**Five**) Questions.

**INSTRUCTION(S) TO CANDIDATES**

**DO NOT OPEN UNTIL YOU ARE ASKED TO DO SO**

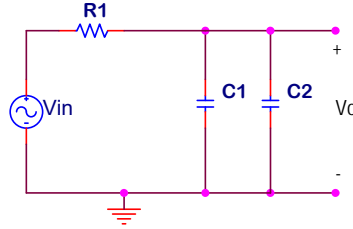
- Total mark of this examination is **100**.
- This examination is worth **50 %** of the total course assessment.
- Answer **ALL QUESTIONS**.
- Only approved calculator with 'KoE approved' sticker is allowed (non-programmable and non-graphical).
- Marks assigned to each problem are listed in the margins.

*Any form of cheating or attempt to cheat is a serious offence which may lead to dismissal.*

*All electronics gadgets are prohibited in the exam hall / venue.  
(e.g. mobile / smart phones, smart watches, and smart glasses)*

**QUESTION 1 (20 marks)**

- (a) Define transfer function of an amplifier. Find the transfer function of the circuit shown in **Fig. 1(a)** and its the corner frequency. What should be the maximum gain of the circuit? (10 marks)

**Fig. 1(a)**

- (b) Draw the frequency response curves, magnitude and phase of the following transfer function by applying Bode plot. (10 marks)

$$H(s) = \frac{10^6 (s + 50)}{s(s + 1)(s + 500)}$$

**QUESTION 2 (20 marks)**

Draw the small signal equivalent circuit diagram of circuit shown in **Fig. 2** which is operating in the midband region of frequencies. The circuit parameters are:  $R_1 = 60 \text{ k}\Omega$ ,  $R_2 = 40 \text{ k}\Omega$ ,  $R_E = 0.4 \text{ k}\Omega$ ,  $R_L = 10 \text{ k}\Omega$ ,  $C_{C1} = 10 \mu\text{F}$ ,  $C_{C2} = \infty$  and  $C_L = 10 \text{ pF}$ . The transistor has small-signal hybrid- $\pi$  parameters,  $r_\pi = 3 \text{ k}\Omega$ ,  $g_m = 40 \text{ mA/V}$  and  $r_o = 100 \text{ k}\Omega$ .

Analyze the circuit by finding the followings:

- (i) The input resistance,  $R_i$ . (2 marks)
- (ii) The output resistance,  $R_o$ . (5 marks)
- (iii) The small signal midband current gain,  $A_i = \frac{i_o}{i_i}$  (5 marks)
- (v) The upper corner frequency due to  $C_{C1} = 10 \mu\text{F}$ . (3 marks)
- (v) The upper corner frequency due to  $C_L = 10 \text{ pF}$ . (3 marks)
- (vii) The bandwidth of the amplifier. (2 marks)

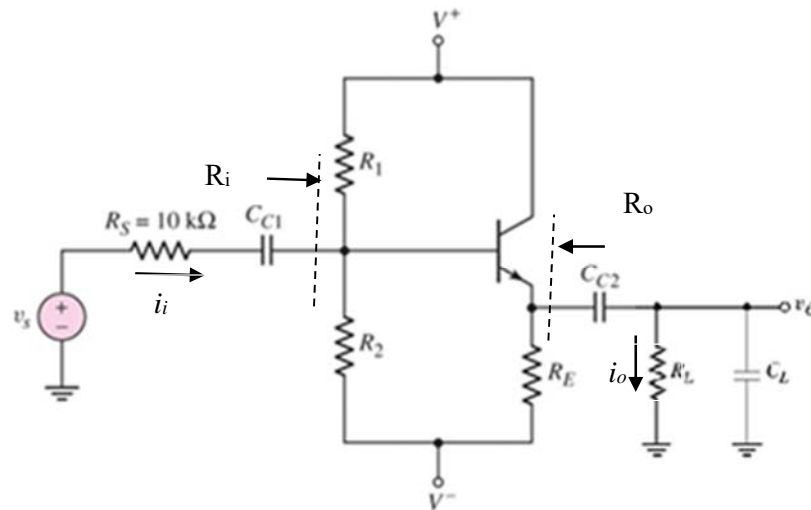


Fig. 2

**QUESTION 3 (20 marks)**

- a) Draw a small signal high frequency equivalent circuit diagram of a short circuited MOSFET amplifier shown in **Fig. 3(a)**. Analyze the circuit step by step and find the short circuit current gain,  $A_i = \frac{i_o}{i_i}$  of the amplifier. What should be the unity gain frequency,  $f_T$  of the amplifier?

(10 marks)

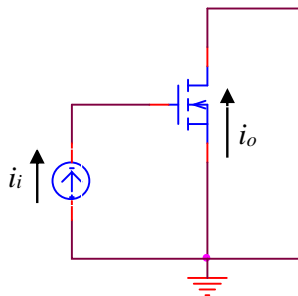


Fig. 3 (a)

- b) A common emitter amplifier is shown in **Fig. 3 (b)** that operates at high frequencies. The circuit parameters are:  $R_s = 2 \text{ k}\Omega$ ,  $R_1 = 33 \text{ k}\Omega$ ,  $R_2 = 22 \text{ k}\Omega$ ,  $R_E = 4 \text{ k}\Omega$ ,  $R_C = 4 \text{ k}\Omega$ ,  $R_L = 5 \text{ k}\Omega$ ,  $C_{C1} = 1 \mu\text{F}$ ,  $C_E = 10 \mu\text{F}$  and  $C_L = 10 \text{ pF}$ . The transistor parameters are:  $g_m = 40 \text{ mA/V}$ ,  $r_\pi = 3 \text{ k}\Omega$  and  $r_o = 100 \text{ K}\Omega$ ,  $C_\pi = 10 \text{ pF}$  and  $C_\mu = 3 \text{ pF}$ .

- (i) Draw the simplified high-frequency small signal equivalent circuit diagram. (2 marks)
- (ii) Evaluate the value of Millar capacitance. (4 marks)
- (iii) Evaluate the upper 3dB frequency ( $f_H$ ) considering Miller capacitance (2 marks)
- (iv) Evaluate the upper 3dB frequency ( $f_H$ ) without considering Miller capacitance. (2 marks)

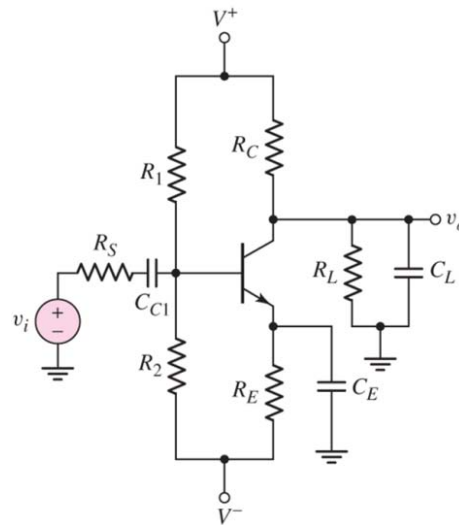
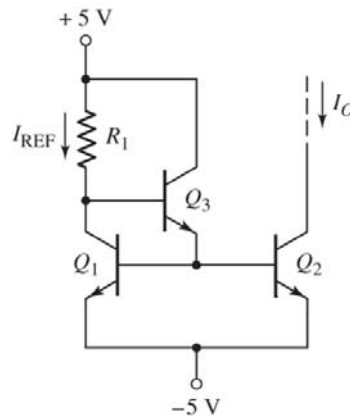


Fig. 3(b)

**QUESTION 4 (20 marks)**

- a) Design a three transistor current source as shown in Fig. 4(a) such that  $I_O = 2$  mA. What is the value of  $I_{REF}$ ? The transistor parameters are:  $V_{BE} (on) = 0.7$  V,  $\beta = 100$  and  $V_A = \infty$ . (5 marks)

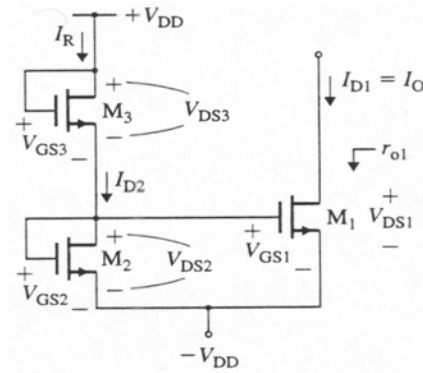


**Fig. 4(a)**

b)

- (i) Design a MOSFET current source as shown in **Fig. 4(b)** such that  $I_R = 25 \text{ mA}$ ,  $I_o = 10 \text{ mA}$ , and  $V_{DS2(\text{sat})} = 0.3 \text{ V}$ . The biasing voltages  $+V_{DD} = +5 \text{ V}$  and  $-V_{DD} = -5 \text{ V}$ . The transistors are available with parameters:  $k'_n = 60 \mu\text{A}/\text{V}^2$ ,  $V_{TN} = 0.4 \text{ V}$  and  $\lambda = 0$ .

(5 marks)

**Fig. 4(b)**

- (ii) Design a new current source using only BJT by converting the MOSFETs.

(2 marks)

- c) The open-loop low-frequency gain of a shunt series amplifier is  $A = 5 \times 10^4$  and the closed-loop gain is  $A_f = 25$ . The open-loop amplifier input resistance,  $R_i = 10 \text{ K}\Omega$  and the output resistance,  $R_o = 100 \Omega$ , what is the value of the input resistance,  $R_{if}$  and output resistance  $R_{of}$  of the closed loop amplifier? What is the value of open loop amplifier bandwidth if the closed loop amplifier bandwidth is 500MHz?

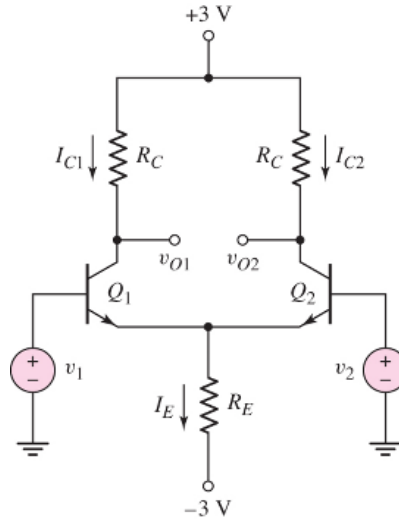
(8 marks)

**QUESTION 5 (20 marks)**

- a) Draw the block diagram and small signal equivalent circuit diagram of a series-series feedback amplifier and identify the amplifier type. Analyze step by step the feedback amplifier by finding the closed loop gain,  $A_f$ , the input resistance,  $R_{if}$  and the output resistance  $R_{of}$  in terms of open-loop amplifier parameters.

(10 marks)

- b) Consider the differential amplifier shown in **Fig. 5(b)** with the transistor parameters  $\beta = 150$ ,  $V_{BE(\text{on})} = 0.7 \text{ V}$  and  $V_A = \infty$ . Design the circuit such that the Q-point values are  $I_{C1} = I_{C2} = 100 \mu\text{A}$  and  $v_{o1} = v_{o2} = 1.2 \text{ V}$  for  $v_1 = v_2 = 0 \text{ V}$ . (5 marks)



**Fig. 5(b)**

- c) A differential amplifier has a differential mode gain of  $A_d = 100$  and the common-mode rejection ratio  $\text{CMRR} = 250$ . Find the differential amplifier output  $v_o$  if the input voltages of the differential amplifiers are  $v_1 = 200 \text{ mV}$  and  $v_2 = 100 \text{ mV}$  (5 marks)

## USEFUL FORMULA

BJT	MOSFET
$i_C = I_S e^{v_{BE}/V_T} \cdot \left(1 + \frac{V_{CE}}{V_A}\right)$ $g_m = \frac{I_{CQ}}{V_T}$ $r_\pi = \frac{\beta V_T}{I_{CQ}}$ $r_o = \frac{V_A}{I_{CQ}}$ $V_T = 26 \text{ mV}$ $V_{BE}(\text{on}) = 0.7 \text{ V}$	$I_D = \frac{1}{2} k'_n \left(\frac{W}{L}\right) (V_{GS} - V_T)^2 (1 + \lambda V_{DS})$ $g_m = 2\sqrt{K_n I_{DQ}}$ $r_o = \frac{1}{\lambda I_{DQ}}$ $K_n = \frac{k'_n}{2} \left(\frac{W}{L}\right)$

END OF PAPER